

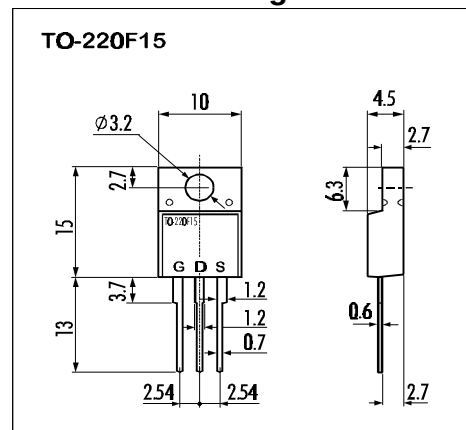
> Features

- High Current
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- High Forward Transconductance
- Avalanche Proof
- Including G-S Zener-Diode

> Applications

- Motor Control
- General Purpose Power Amplifier
- DC-DC Converters

> Outline Drawing

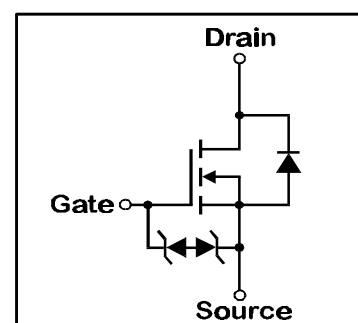


> Maximum Ratings and Characteristics

- Absolute Maximum Ratings ($T_C=25^\circ\text{C}$), unless otherwise specified

Item	Symbol	Rating	Unit
Drain-Source-Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	20	A
Pulsed Drain Current	$I_{D(puls)}$	80	A
Continuous Reverse Drain Current	I_{DR}	20	A
Gate-Source-Voltage	V_{GS}	± 20	V
Max. Power Dissipation	P_D	35	W
Operating and Storage Temperature Range	T_{ch}	150	$^\circ\text{C}$
	T_{stg}	-55 ~ +150	$^\circ\text{C}$

> Equivalent Circuit



- Electrical Characteristics ($T_C=25^\circ\text{C}$), unless otherwise specified

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown-Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$ $V_{GS}=0\text{V}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$I_D=1\text{mA}$ $V_{DS}=V_{GS}$	1,0	1,5	2,0	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{V}$ $T_{ch}=25^\circ\text{C}$			500	μA
		$V_{GS}=0\text{V}$ $T_{ch}=125^\circ\text{C}$			1,0	mA
Gate Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$ $V_{DS}=0\text{V}$			10	μA
Drain Source On-State Resistance	$R_{DS(on)}$	$I_D=10\text{A}$ $V_{GS}=4\text{V}$		0,09	0,11	Ω
		$I_D=10\text{A}$ $V_{GS}=10\text{V}$		0,055	0,07	Ω
Forward Transconductance	g_{fs}	$I_D=10\text{A}$ $V_{DS}=25\text{V}$	6	12		S
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}$		600	900	pF
Output Capacitance	C_{oss}	$V_{GS}=0\text{V}$		260	390	pF
Reverse Transfer Capacitance	C_{rss}	$f=1\text{MHz}$		150	240	pF
Turn-On-Time t_{on} ($t_{on}=t_{d(on)}+t_r$)	$t_{d(on)}$	$V_{CC}=30\text{V}$		7	11	ns
	t_r	$I_D=20\text{A}$		30	45	ns
Turn-Off-Time t_{off} ($t_{off}=t_{d(off)}+t_f$)	$t_{d(off)}$	$V_{GS}=10\text{V}$		100	150	ns
	t_f	$R_{GS}=25\Omega$		70	110	ns
Diode Forward On-Voltage	V_{SD}	$I_F=2 \times I_{DR}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		1,45	2,18	V
Reverse Recovery Time	t_{rr}	$I_F=I_{DR}$ $V_{GS}=0\text{V}$		90	130	ns
		$-di_F/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$				

- Thermal Characteristics

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Thermal Resistance	$R_{th(ch-a)}$	channel to air			62,5	$^\circ\text{C}/\text{W}$
	$R_{th(ch-c)}$	channel to case			3,57	$^\circ\text{C}/\text{W}$

N-channel MOS-FET

60V 0,07Ω 20A 35W

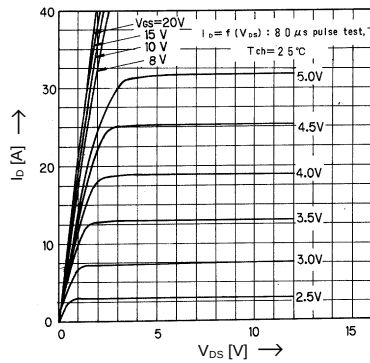
2SK1822-01M

FAP-III A Series

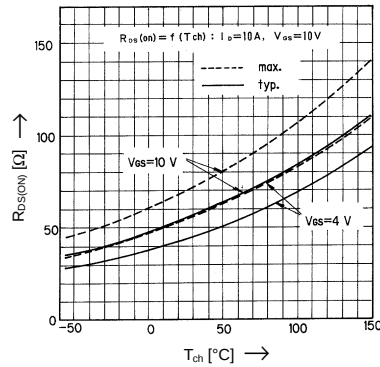
FUJI
ELECTRIC

> Characteristics

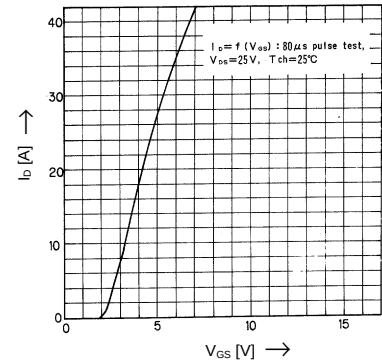
Typical Output Characteristics



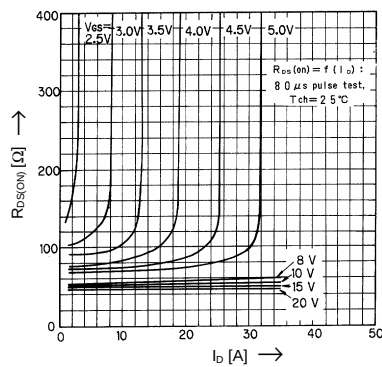
Drain-Source-On-State Resistance vs. T_{ch}



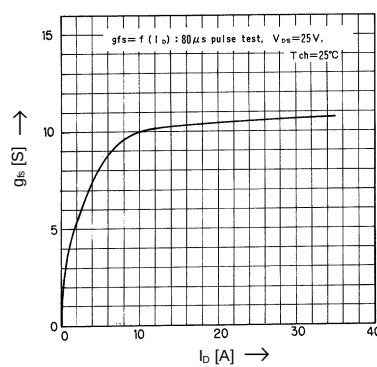
Typical Transfer Characteristics



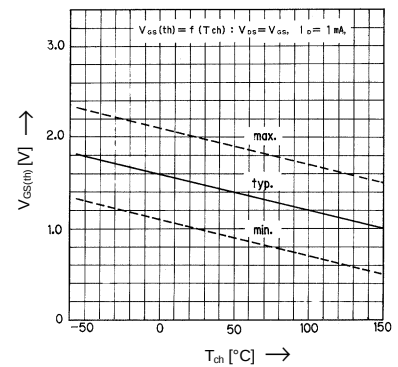
Typical Drain-Source-On-State-Resistance vs. I_D



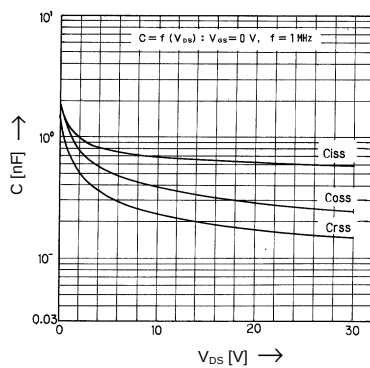
Typical Forward Transconductance vs. I_D



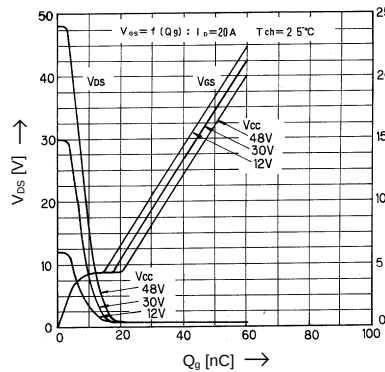
Gate Threshold Voltage vs. T_{ch}



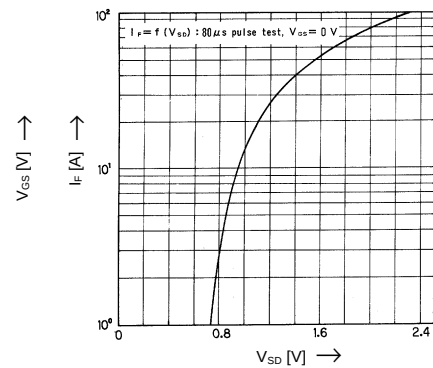
Typical Capacitance vs. V_{DS}



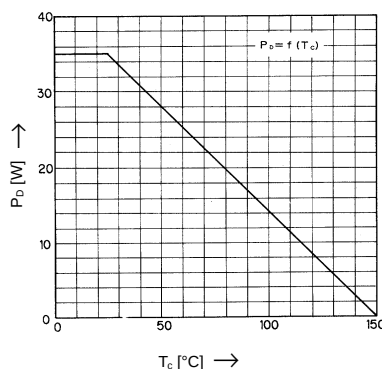
Typical Input Charge



Forward Characteristics of Reverse Diode



Allowable Power Dissipation vs. T_c



Safe operation area

